	Application No.	Applicant(s)
	10/755,498	CHAN ET AL.
Notice of Allowability	Examiner	Art Unit
	DuyVu n. Deo	1765
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) of NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIC of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED in this appropriate communication.  This appropriate communication is subject.	oplication. If not included n will be mailed in due course. <b>THIS</b>
1. This communication is responsive to amendment filed 8/15/	<u>′05</u> .	·
2. The allowed claim(s) is/are <u>28-35</u> .		
3. Acknowledgment is made of a claim for foreign priority und a) All b) Some* c) None of the:  1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMETHIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which gives	been received. been received in Application No uments have been received in this of this communication to file a reply ENT of this application.  tted. Note the attached EXAMINE	s national stage application from the y complying with the requirements
<ol> <li>CORRECTED DRAWINGS ( as "replacement sheets") must (a)  including changes required by the Notice of Draftsperson (b)  including changes required by the attached Examiner's Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR 1.1 each sheet. Replacement sheet(s) should be labeled as such in the</li> </ol>	on's Patent Drawing Review (PTC Amendment / Comment or in the	Office action of rings in the front (not the back) of
6. DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT F		
<ul> <li>Attachment(s)</li> <li>1. ☑ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date 2/25/04</li> <li>4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material</li> </ul>	6. ☐ Interview Summar Paper No./Mail D B), 7. ⊠ Examiner's Amend	ate

## **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

On page 1 of the specification, after the title, please insert—This is a Continuation of Patent Application serial number 10/054,561, filling date 1/22/02, now U.S. Patent # 6,706,591, Method of Forming a Stacked Capacitor Structure with Increased Surface Area for a Dram Device, assigned to the same assignee as the present invention.

## Allowable Subject Matter

2. The following is an examiner's statement of reasons for allowance: prior art doesn't suggest or teach a second portion of said storage node shape overlies portions of a top surface of said insulator layer; said storage node shape having alternate rows of doped regions therein that are aligned horizontally and parallel to the top surface of said insulator layer, and having alternate rows of undoped regions therein that are also aligned horizontally and parallel to the top surface of said insulator layer, with each set of said doped regions separated by and a respective one of said undoped regions; said storage node shape further having lateral grooves extending inwards from sides of each said doped region in said storage node shape, and wherein each said undoped region of said storage node shape exhibits smooth, non-groove sides a capacitor dielectric layer located on a smooth top surface of, and on sides of said storage node shape, and

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wherein said capacitor dielectric layer conforms to contour of the surfaces of the lateral grooves in each said doped region of said storage node shape.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to DuyVu n. Deo whose telephone number is 571-272-1462. The examiner can normally be reached on 6:00-2:30 Mon-Fri.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Primary Examiner

Duy-Vu Deo 10/31/05